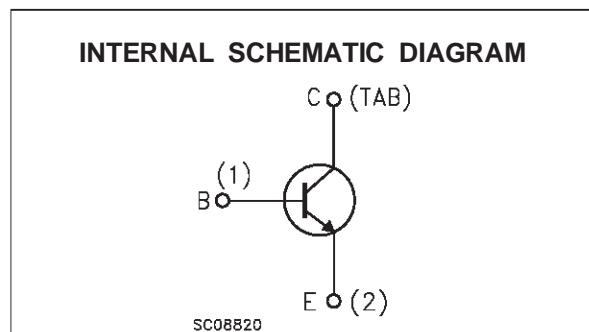
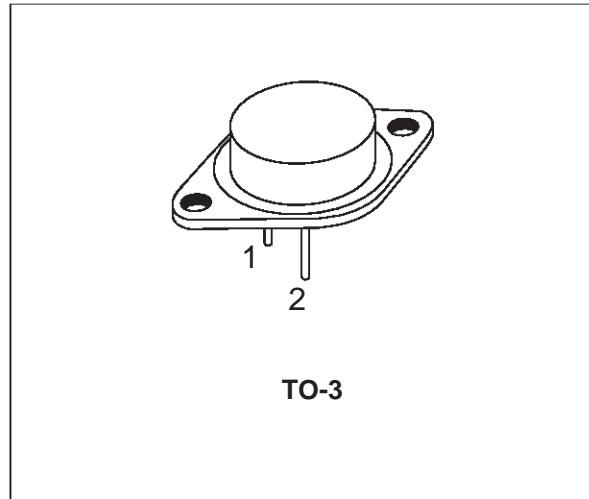


HIGH CURRENT NPN SILICON TRANSISTOR

- STMicroelectronics PREFERRED SALES TYPE
- NPN TRANSISTOR

DESCRIPTION

The 2N5038 is a silicon planar multiepitaxial NPN transistors in Jedec TO-3 metal case. They are especially intended for high current and switching applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	150	V
V_{CEX}	Collector-Emitter Voltage ($V_{BE}=-1.5V$ $R_{BE}=100\Omega$)	150	V
V_{CER}	Collector-Emitter Voltage ($R_{BE} < 50\Omega$)	110	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	90	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	7	V
I_C	Collector Current	20	A
I_{CM}	Collector Peak Current	30	A
I_B	Base Current	5	A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ C$	140	W
T_{stg}	Storage Temperature	-65 to 200	°C

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	1.25	$^{\circ}\text{C/W}$
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \ ^{\circ}\text{C}$ unless otherwise specified)

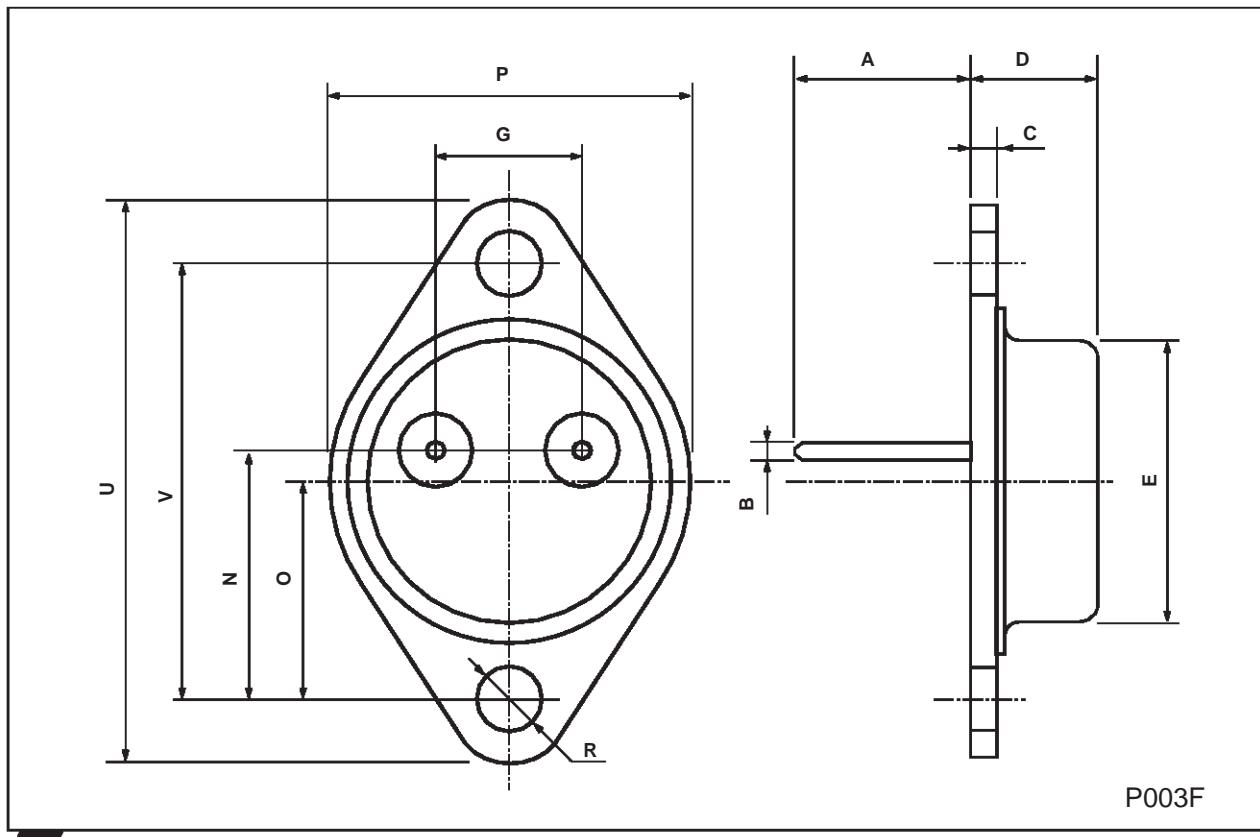
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEV}	Collector Cut-off Current ($V_{BE} = -1.5\text{V}$)	$V_{CE} = 140 \text{ V}$ $V_{CE} = 100 \text{ V} \quad T_c = 150 \ ^{\circ}\text{C}$			50 10	mA mA
I_{CEO}	Collector Cut-off Current ($I_B = 0$)	$V_{CE} = 70 \text{ V}$			20	mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 7 \text{ V}$ $V_{EB} = 5 \text{ V}$			50 5	mA mA
$V_{CEO(sus)*}$	Collector-Emitter Sustaining Voltage	$I_C = 0.2 \text{ A}$	90			V
$V_{CER(sus)*}$	Collector-Emitter Sustaining Voltage	$I_C = 0.2 \text{ A} \quad R_{BE} = 50 \Omega$	110			V
$V_{CEX(sus)*}$	Collector-Emitter Sustaining Voltage	$I_C = 0.2 \text{ A} \quad R_{BE} = 100 \Omega \quad V_{BE} = -1.5\text{V}$	150			V
$V_{CE(sat)*}$	Collector-Emitter Saturation Voltage	$I_C = 12 \text{ A} \quad I_B = 1.2 \text{ A}$ $I_C = 20 \text{ A} \quad I_B = 5 \text{ A}$			1 2.5	V V
$V_{BE(sat)*}$	Collector-Emitter Saturation Voltage	$I_C = 20 \text{ A} \quad I_B = 5 \text{ A}$			3.3	V
V_{BE*}	Base-Emitter Voltage	$I_C = 12 \text{ A} \quad V_{CE} = 5 \text{ V}$			1.8	V
h_{FE*}	DC Current Gain	$I_C = 2 \text{ A} \quad V_{CE} = 5 \text{ V}$ $I_C = 12 \text{ A} \quad V_{CE} = 5 \text{ V}$	50 20		250 100	
h_{fe}	Small Signal Current Gain	$I_C = 2 \text{ A} \quad V_{CE} = 10 \text{ V} \quad f = 5 \text{ MHz}$	12			
C_{CBO}	Collector-Base Capacitance	$I_E = 0 \quad V_{CB} = 10 \text{ V} \quad f = 1 \text{ MHz}$			300	pF
t_r t_s t_f	Rise Time Storage Time Fall Time	$I_C = 12 \text{ A} \quad V_{CC} = 30 \text{ V}$ $I_{B1} = -I_{B2} = 1.2\text{A}$			0.5 1.5 0.5	μs μs μs
$I_{s/b}^{**}$	Second Breakdown Collector Current	$V_{CE} = 28 \text{ V}$ $V_{CE} = 45 \text{ V}$	5 0.9			A A
$E_{s/b}$	Second Breakdown Energy	$V_{BE} = -4 \text{ V} \quad R_{BE} = 20 \Omega \quad L = 180\mu\text{H}$	13			mJ

* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

** Pulsed: 0.5 s non repetitive pulse.

TO-3 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



P003F

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